

MM54HC7266/MM74HC7266 Quad 2-Input Exclusive NOR Gate

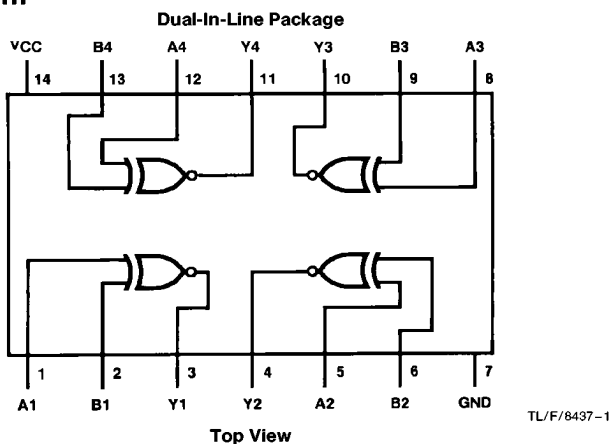
General Description

This exclusive NOR gate utilizes advanced silicon-gate CMOS technology to achieve operating speeds similar to equivalent LS-TTL gates while maintaining the low power consumption and high noise immunity characteristic of standard CMOS integrated circuits. These gates are fully buffered and have a fanout of 10 LS-TTL loads. The MM54HC/MM74HC logic family is functionally as well as pin out compatible with the standard 54LS/74LS logic family. However, unlike the 'LS266, which is an open collector gate, the 'HC266 has standard CMOS push-pull outputs. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 9 ns
- Wide operating voltage range: 2–6V
- Low input current: 1 μ A maximum
- Low quiescent current: 20 μ A maximum (74 Series)
- Output drive capability: 10 LS-TTL loads
- Push-pull output

Connection Diagram



Order Number MM54HC7266 or MM74HC7266

Truth Table

Inputs		Outputs
A	B	Y
L	L	H
L	H	L
H	L	L
H	H	H

$$Y = A \oplus B = AB + \bar{A}\bar{B}$$

MM54HC7266/MM74HC7266 Quad 2-Input Exclusive NOR Gate

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} + 1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} + 0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
V_{CC} = 2.0V		1000	ns
V_{CC} = 4.5V		500	ns
V_{CC} = 6.0V		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC	54HC	Units
						T _A = −40°C to 85°C	T _A = −55°C to 125°C	
				Typ	Guaranteed Limits			
V _{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V _{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V _{OH}	Minimum High Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	2.0	1.9	1.9		V
			4.5V	4.5	4.4	4.4		V
			6.0V	6.0	5.9	5.9		V
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V _{OL}	Maximum Low Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND I _{OUT} = 0 μA	6.0V		2.0	20	40	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

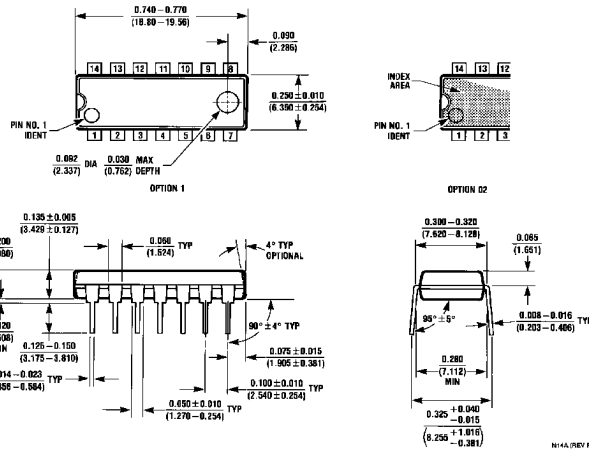
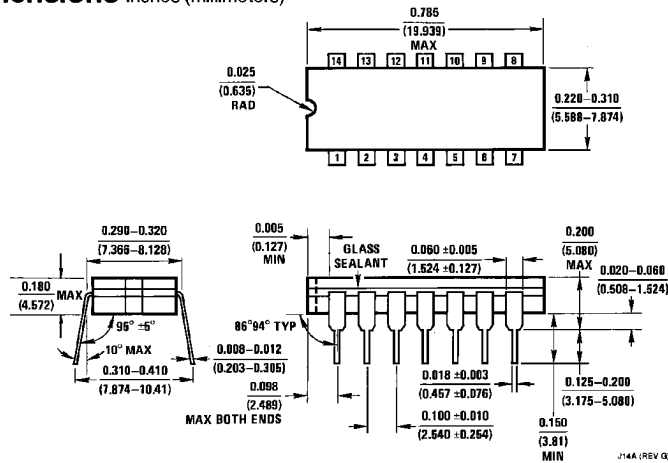
AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25^\circ C$, $C_L = 15\text{ pF}$, $t_r = t_f = 6\text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay		12	20	ns

AC Electrical Characteristics $V_{CC} = 2.0V$ to $6.0V$, $C_L = 50\text{ pF}$, $t_r = t_f = 6\text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC T _A = −40°C to 85°C		54HC T _A = −55°C to 125°C		Units
				Typ	Guaranteed Limits					
t _{PHL} , t _{PLH}	Maximum Propagation Delay		2.0V	60	120	151		179		ns
			4.5V	12	24	30		36		ns
			6.0V	10	20	26		30		ns
t _{THL} , t _{TLH}	Maximum Output Rise and Fall Time		2.0V	30	75	95		110		ns
			4.5V	8	15	19		22		ns
			6.0V	7	13	16		19		ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		25						pF
C _{IN}	Maximum Input Capacitance			5	10	10		10		pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Physical Dimensions inches (millimeters)**LIFE SUPPORT POLICY**

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor Corporation
1111 West Bardin Road
Arlington, TX 76017
Tel: 1(800) 272-9959
Fax: 1(800) 737-7018

National Semiconductor Europe
Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2406

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.